

N & P-Channel 40-V (D-S) MOS FET

Features

- Low rDS(on) trench technology
- Low thermal impedance
- Fast switching speed

Typical Applications:

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

Package type: SO-8

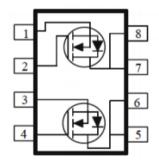
Packing & Order Information

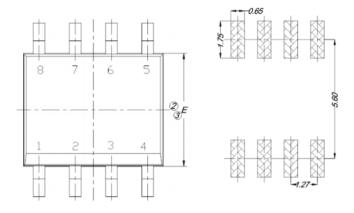
3,000/Reel

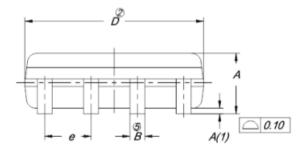


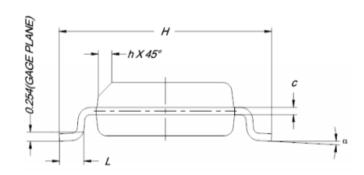
RoHS COMPLIANT

Graphic symbol









DI14	MILLIMETERS				
DIM.	MIN.	NOM.	MAX.		
Α	1.35	1.55	1.75		
A(1)	0.10	0.18	0.25		
В	0.38	0.45	0.51		
С	0.19	0.22	0.25		
D	4.80	4.90	5.00		
E	3.80	3.90	4.00		
е	1.27 BSC				
Н	5.80	6.00	6.20		
L	0.50	0.72	0.93		
α	0°	4°	8°		
h	0.25	0.38	0.50		



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MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

THE RESIDENCE THE PROPERTY OF					
Absolute Maximum Ratings (T _A =25°C unless otherwise specified)					
Symbol	Parameter	Nch	Pch	Unit	
V_{DS}	Drain-Source Voltage	40	-40	V	
V_{GS}	Gate-Source Voltage	±20	±20	V	
T_	Continuous Drain Current ^a (T _A =25°C)	5.8	-3.9	A	
I _D	Continuous Drain Current ^a (T _A =70°C)	4.5	-3.1	A	
I_{DM}	Pulsed Drain Current ^b	20	-20	A	
Is	Continuous Source Current (Diode Conduction) ^a	2.6	-2.5	A	
P _D	Power Dissipation ^a (T _A =25°C)	2.1	2.1	W	
	Power Dissipation ^a (T _A =70°C)	1.3	1.3	W	
T _J /T _{STG}	Operating Junction and Storage Temperature	-55 to 150 °C		°C	

Thermal Resistance Ratings						
Symbol	Parameter	Maximum	Units			
RөлA	Maximum Junction-to-Ambient ^a (t <= 10 sec)	62.5	°C/W			
	Maximum Junction-to-Ambient ^a (Steady-State)	110	C/ vv			

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Static						
Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
V	Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A \text{ (N-ch)}$	1			***
V _{GS(th)}		$V_{DS} = V_{GS}, I_D = -250 \mu A (P-ch)$	-1			V
I_{GSS}	Gate-Body Leakage	$V_{DS} = 0 V$, $V_{GS} = \pm 20 V$			±100	nA
I	Zero Gate Voltage Drain Current	$V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V (N-ch)}$			1	uA
I _{DS S}		$V_{DS} = -32 \text{ V}, V_{GS} = 0 \text{ V (P-ch)}$			-1	
т	On-State Drain Current	$V_{DS} = 5 \text{ V}, V_{Gs} = 10 \text{ V} (N-ch)$	10			A
I _{D(on)}		$V_{DS} = -5 \text{ V}, V_{Gs} = -10 \text{ V (P-ch)}$	-10			
	Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 5.3 \text{ A (N-ch)}$			42	mΩ
r _{DG(}		$V_{GS} = 4.5 \text{ V}, I_D = 4.4 \text{ A (N-ch)}$			60	
^r DS(on)		$V_{GS} = -10 \text{ V}, I_D = -3.6 \text{ A (N-ch)}$			90	
		$V_{GS} = -4.5 \text{ V}, I_D = -2.6 \text{ A (N-ch)}$			125	
g fs	Forward Tranconductance	$V_{GS} = 15 \text{ V}, I_D = 5.3 \text{ A (N-ch)}$		13		S
		$V_{GS} = -15 \text{ V}, I_D = -3.6 \text{ A (P-ch)}$		11		
V_{SD}	Die le Ferrand Walter	$I_S = 1.3 A$, $V_{GS} = 0 V$ (N-ch)		0.77		V
	Diode Forward Voltage	$I_S = -1.2 A$, $V_{GS} = 0 V (P-ch)$		-0.81		V



MS 45 C 41

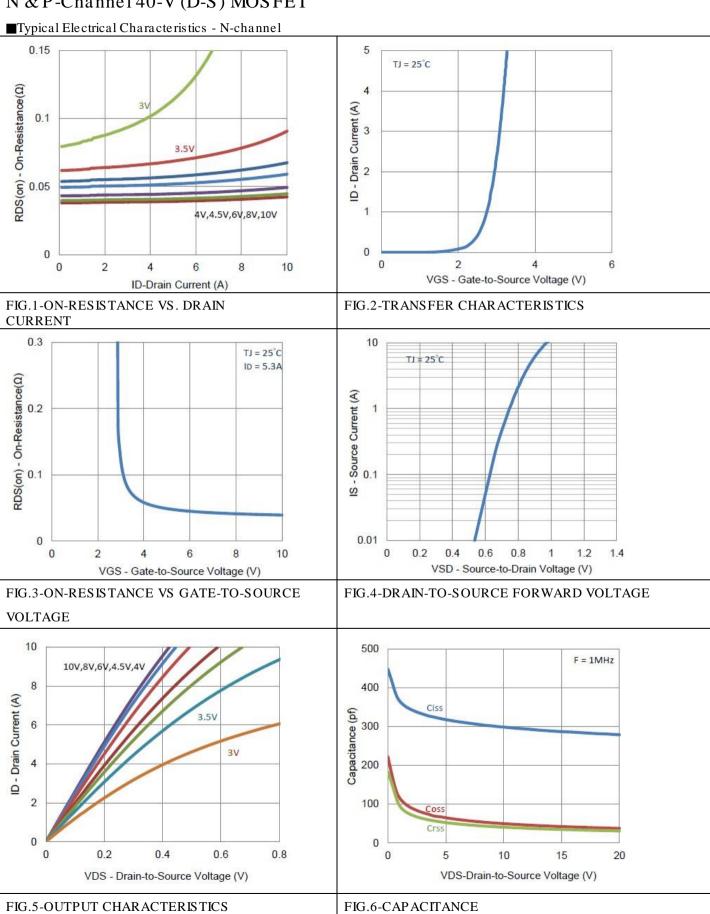
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Dynamic ^b						
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units
Qg	Total Gate Charge	N-Channel		3.6		nC
Q_{gs}	Gate-Source Charge	$V_{DS} = 20 \text{ V}, I_D = 5.3 \text{ A},$		1.3		nC
Q_{gd}	Gate-Drain Charge	$V_{GS} = 10 \text{ V}$		1.4		nC
t _{d(on)}	Turn-On Delay Time	N-Channel		2		ns
t _r	Rise Time	$I_D = 5.3 \text{ A}, R_L = 3.5 \Omega,$		18		ns
t _{d(off)}	Turn-Off Delay Time	$V_{GEN} = 10 \text{ V}$, $R_{GEN} = 6 \Omega$		16		ns
tf	Fall Time	$V_{DD} = 20 \text{ V}$		5		ns
C _{ISS}	Input Capacitance	N-Channel		287		pF
Coss	Output Capacitance	$V_{DS} = 15 \text{ V}$		42		pF
C _{RSS}	Reverse Transfer Capacitance	$f = 1 \text{ MHz }, V_{GS} = 0 \text{ V}$		34		pF
Qg	Total Gate Charge	P-Channel		5.8		nC
Q_{gs}	Gate-Source Charge	$V_{DS} = -20 \text{ V}$, $I_D = -3.6 \text{ A}$,		1.6		nC
Q_{gd}	Gate-Drain Charge	$V_{GS} = -10 \text{ V}$		2.3		nC

Dynamic ^b						
Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
t _{d(on)}	Turn-On Delay Time	P-Channel		4		ns
$t_{\rm r}$	Rise Time	$I_D = -3.6 \text{ A}, R_L = 5.5 \Omega,$		5		ns
t _{d(off)}	Turn-Off Delay Time	V_{GEN} = -10 V, R_{GEN} = 6 Ω		17		ns
tf	Fall Time	$V_{DD} = -20 \text{ V}$		7		ns
Ciss	Input Capacitance	P-Channel		384		pF
Coss	Output Capacitance	$V_{DS} = -15 \text{ V}$		36		pF
Crss	Reverse Transfer Capacitance	$f = 1 \text{ MHz }, V_{GS} = 0 \text{ V}$		36		pF



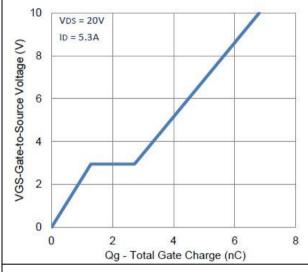
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■Typical Electrical Characteristics - N-channel



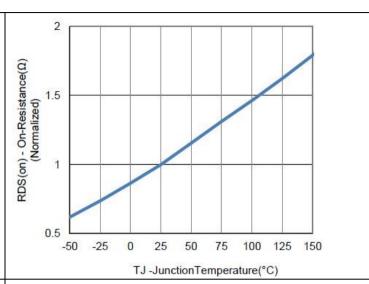


FIG.7-GATE CHARGE

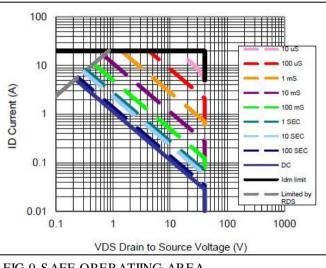


FIG.8-NORMALIZED ON-RESISTANCE VS JUNCTION TEMPERATURE

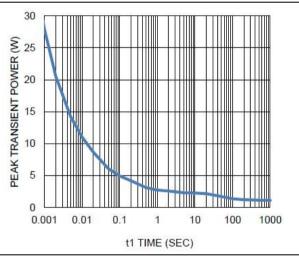


FIG.9-SAFE OPERATIING AREA



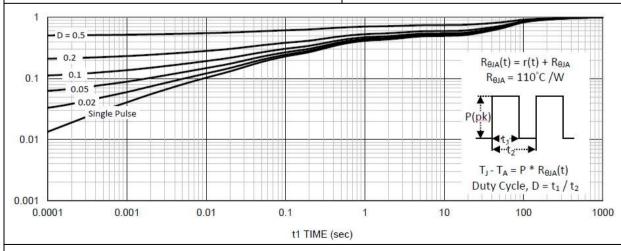
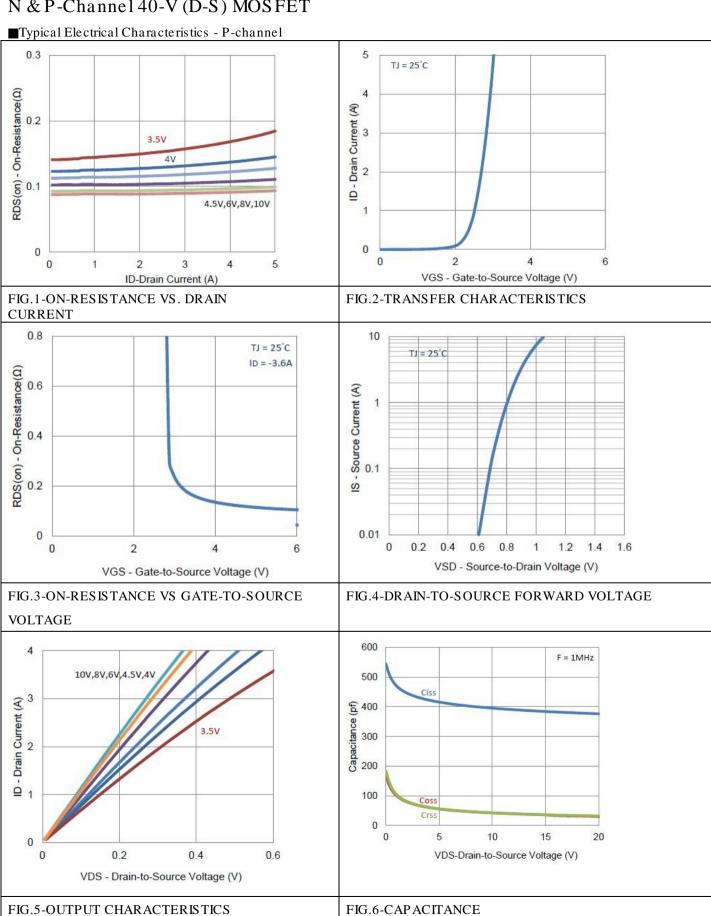


FIG.11-NORMALIZED THERMAL TRANSIENT JUNCTION TO AMBIENT

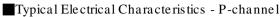


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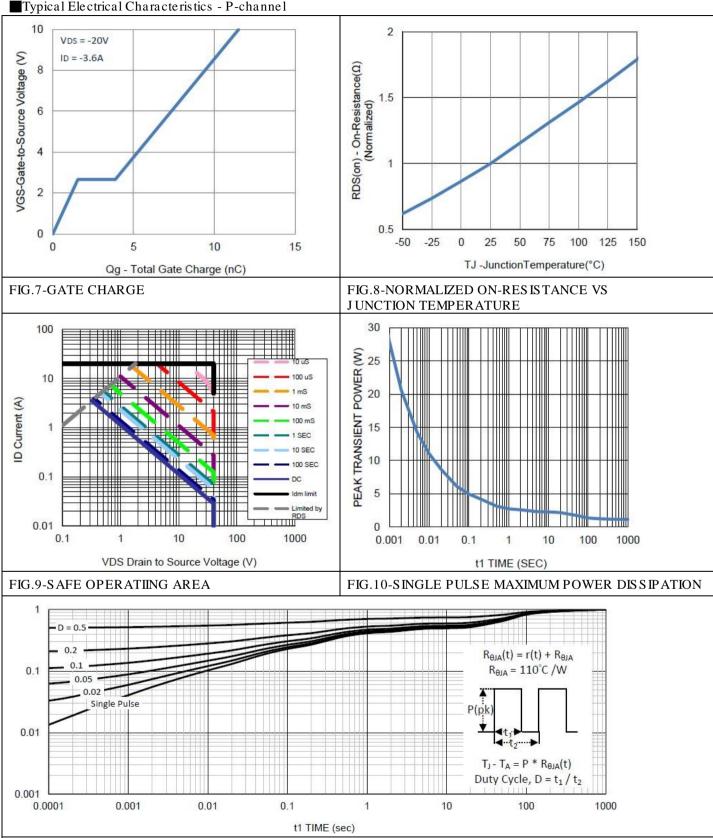


FIG.11-NORMALIZED THERMAL TRANSIENT JUNCTION TO AMBIENT



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